

2SC2027

High-reliability discrete products and engineering services since 1977

SILICON NPN TRANSISTOR

FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

MAXIMUM RATINGS

Parameter	Symbol	2SC2027	Unit
Collector-base voltage	V _{CBO}	1500	V
Collector-emitter voltage	V _{CEO}	800	V
Emitter-base voltage	V _{EBO}	5.0	V
Collector current – continuous	lc	5	A
Collector current – peak ⁽¹⁾	Ісм	7.5	A
Total power dissipation	PD	50	W
Junction temperature	TJ	175	°C
Storage temperature range	T _{stg}	-65 to 200	°C

ELECTRICAL CHARACTERISTICS (T_c = 25°C unless otherwise noted)

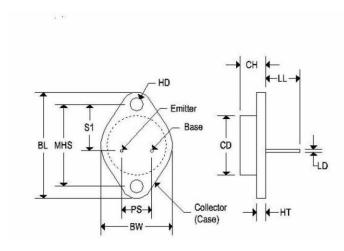
Parameter	Symbol	Conditions	2SC1325A			11
			Min	Тур	Max	Unit
Collector-emitter breakdown voltage	V _{CEO(sus)}	$I_{C} = 0.1A$, $I_{B} = 0$	800	-	-	V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 1mA, I _C = 0	5	-	-	V
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 4.0A, I _B = 1.3A	-	-	5.0	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = 4.0A, I _B = 1.3A	-	-	1.5	V
Collector cutoff current	I _{CBO}	$V_{CB} = 600V, I_E = 0$	-	-	10	μA
Emitter cutoff current	I _{EBO}	$V_{EB} = 5V, I_{C} = 0$	-	-	10	μA
DC current gain	hff	I _C = 1.0A, V _{CE} = 5V	8	-	36	_
	IIFE	I _C = 4.5A, V _{CE} = 5V	2.25	-	-	-



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MECHANICAL CHARACTERISTICS

Case:	ТО-3
Marking:	Alpha-Numeric
Polarity:	See below



	TO-3				
	Inches		Millimeters		
	Min	Max	Min	Max	
CD	-	0.875		22.220	
CH	0.250	0.380	6.860	9.650	
HT	0.060	0.135	1.520	3.430	
BW	-	1.050		26.670	
HD	0.131	0.188	3.330	4.780	
LD	0.038	0.043	0.970	1.090	
LL	0.312	0.500	7.920	12.700	
BL	1.550 REF		39.370 REF		
MHS	1.177	1.197	29.900	30.400	
PS	0.420	0.440	10.670	11.180	
S1	0.655	0.675	16.640	17.150	

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